# Half Slim

## SHE1B



#### **GENERAL INFORMATION**

MTBF         ≥ 2,000,000 hours           SHOCK         1500G,0.5ms           VIBRATION         20G,10-2000Hz           HUMIDITY         0 to 90 % RH (No condensation)           ELECTRICAL DATA         5 V ± 10 %           POWER CONSUMPTION         - Read: 250mA max.           - Write: 270mA max.         - Slumber: less than 100mA	GENERAL IN OTHER TON			
DATA TRANSFER MODE   SATA 1.5Gbps, 3.0Gbps	TYPE	Half Slim		
CONNECTOR         15 + 7 pin Serial ATA           OUTLINE DIMENSIONS         54 × 39 mm           SERIES         SHETB           CONTROLLER TYPE         TDK GBDriver GS1           FLASH TYPE         SLC         pSLC:MLC           DENSITY RANGE         16 GB - 128 GB         MLC:32GB-256GB           DATA RETENTION         10 years @ life begin-109%           ENDURANCE         100,000 P/E Cycles         pSLC:20,000 P/E Cycles           ENTERPRISE WL         "Flash Block Level         MLC:3,000 P/E Cycles           "Flash Block Level         "Flash Block Level         "Flash Block Level           TEMPERATURE           OPERATING TEMPERATURE         Commercial: 0°C to +70°C Industrial: -40°C to +85°C Industrial: -40°C to +85°C           STORAGE TEMPERATURE         Commercial: 22°C to +85°C           PERFORMANCE           PERFORMANCE           PERFORMANCE           Read (max)         340 MByte/sec         pSLC:400 MByte/sec           Write (max)         115 MByte/sec         pSLC:105 MByte/sec           MILC:320 MByte/sec         MLC:75 MByte/sec           MTEF         ≥ 2,000,000 hours         sHAT           SHOCK         1500G,0 5ms           VIBRATION	INTERFACE	Serial ATA Revision 3.1		
SERIES   SHE'S	DATA TRANSFER MODE	SATA 1.5Gbps, 3.0Gbps, 6.0Gbps		
SERIES	CONNECTOR			
TDK GBDriver GS1	OUTLINE DIMENSIONS	54 x 39 mm		
DENSITY PRANCE		SHE1B		
DENSITY RANGE   16 GB - 128 GB	CONTROLLER TYPE OGBDriver	TDK GBDriver GS1		
DENSITY HANGE   16 GB - 128 GB	FLASH TYPE	SLC	·	
DATA RETENTION	DENSITY RANGE	16 GB - 128 GB	•	
## ENDURANCE ENTERPRISE WILL ## 100,000 P/E Cycles ENTERPRISE WILL ## 100,000 P/E Cycles ## 100,000 P/E	DATA DETENTION	10 years @ life begin-10%		
ENTERPRISE W. "Flash Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Level Tells" Constitution (a. 45° C to +85° C   **Total Block Le	DATA RETENTION			
### TEMPERATURE  OPERATING TEMPERATURE  OPERATING TEMPERATURE  STORAGE TEMPERATURE  Commercial: -26°C to +85°C  Commercial: -26°C to +85°C  STORAGE TEMPERATURE  Commercial: -26°C to +85°C  STORAGE TEMPERATURE  Commercial: -26°C to +85°C  PERFORMANCE  Read (max.)  340 MByte/sec  MLC:320 MByte/sec	ENDURANCE	100 000 P/F Cycles	pSLC:20,000P/ECycles	
TEMPERATURE  OPERATING TEMPERATURE  STORAGE TEMPERATURE  STORAGE TEMPERATURE  Commercial: -40°C to +85°C  STORAGE TEMPERATURE  Commercial: -25°C to +85°C  Industrial: -40°C to +85°C  PERFORMANCE  Read (max.)  340 MByte/sec  MLC:320 MByte/sec  MLC:320 MByte/sec  MLC:75 MByte/sec  MLC:75 MByte/sec  MLC:75 MByte/sec  MTBF  ≥ 2,000,000 hours  SHOCK  1500G,0.5ms  VIBRATION  20G,10-2000Hz  HUMIDITY  0 to 90 % RH (No condensation)  ELECTRICAL DATA  VOLTAGE  POWER CONSUMPTION  - Read: 250mA max Write: 270mA max Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Back-up Circuit - Global static wear leveling - SMART - NCG, TRIM - AES 128/256bit encryption		-		
Commercial: 0°C to +70°C   Industrial: -40°C to +85°C			*Flash Block Level	
STORAGE TEMPERATURE	TEMPERATURE			
STORAGE TEMPERATURE   Commercial: -25°C to +85°C     Industrial: -40°C to +85°C     PERFORMANCE     Read (max.)   340 MByte/sec   pSLC:400 MByte/sec     MLC:320 MByte/sec   pSLC:165 MByte/sec     MLC:75 MByte/sec   MLC:75 MByte/sec     MLC:75 MByte/sec   MLC:75 MByte/sec     MTBF   ≥ 2,000,000 hours     SHOCK   1500Q.0.5ms     VIBRATION   20G.10-2000Hz     HUMIDITY   0 to 90 % RH (No condensation)     ELECTRICAL DATA     VOLTAGE   5 V ± 10 %     POWER CONSUMPTION   - Read: 250mA max.	OPERATING TEMPERATURE			
Industrial: -40°C to +85°C				
PERFORMANCE           Read (max.)         340 MByte/sec         pSLC:400 MByte/sec MLC:320 MByte/sec MLC:320 MByte/sec pSLC:165 MByte/sec pSLC:165 MByte/sec MLC:75 MByte/sec MLC:75 MByte/sec MLC:75 MByte/sec           ROBUSTNESS         MTBF         ≥ 2,000,000 hours           SHOCK         1500G,0.5ms           VIBRATION         20G,10-2000Hz           HUMIDITY         0 to 90 % RH (No condensation)           ELECTRICAL DATA         5 V ± 10 %           FOWER CONSUMPTION           - Read: 250mA max Write: 270mA max Write: 270mA max Slumber: less than 100mA           - FEATURE LIST         - In-House Designed Controller (HW/FW) - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIIM - NCQ, TRIIM - NCQ, TRIIM - AES 128/256bit encryption	STORAGE TEMPERATURE			
Read (max.)   340 MByte/sec	DEDECRMANOE	industriai: -4t	J C 10 +85 C	
### Write (max.)  ### Write (max.)  ### Write (max.)  ### ### Write (max.)  ### ### Write (max.)  ### ### ### ### ### ### ### ### ### #	PERFORMANCE		nSLC : 400 MPyto/200	
Write (max.)         115 MByte/sec         pSLC:165 MByte/sec MLC:75 MByte/sec MLC:75 MByte/sec           ROBUSTNESS         MTBF         ≥ 2,000,000 hours           SHOCK         1500G,0.5ms         VIBRATION           VIBRATION         20G,10-2000Hz         HUMIDITY         0 to 90 % RH (No condensation)           ELECTRICAL DATA         VOLTAGE         5 V ± 10 %           - Read: 250mA max Write: 270mA max Write: 270mA max Slumber: less than 100mA           - FEATURE LIST           - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - NCQ, TRIM - NCQ, TRIM - AES 128/256bit encryption	Read (max.)	340 MByte/sec		
### MEC: 76 MByte/sec  #### Nobustness    MTBF	Marita (es sur)	ddC MD:do/coo		
MTBF         ≥ 2,000,000 hours           SHOCK         1500G,0.5ms           VIBRATION         20G,10-2000Hz           HUMIDITY         0 to 90 % RH (No condensation)           ELECTRICAL DATA         VOLTAGE         5 V ± 10 %           POWER CONSUMPTION         - Read: 250mA max.           - Write: 270mA max.         - Slumber: less than 100mA           FEATURE LIST           - In-House Designed Controller (HW/FW)           - Power Fail Data Safety         - Power Back-up Circuit           - Global static wear leveling         - SMART           - NCQ, TRIM         - AES 128/256bit encryption	Write (max.)	115 MByte/sec	MLC:75 MByte/sec	
SHOCK	ROBUSTNESS			
VIBRATION  PUMIDITY  0 to 90 % RH (No condensation)  ELECTRICAL DATA  VOLTAGE  5 V ± 10 %  - Read: 250mA max Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	MTBF			
### POWER CONSUMPTION    POWER CONSUMPTION	SHOCK			
POWER CONSUMPTION  - Read: 250mA max Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	VIBRATION			
POWER CONSUMPTION  - Read: 250mA max Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	HUMIDITY	0 to 90 % RH (No condensation)		
- Read: 250mA max Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	ELECTRICAL DATA			
POWER CONSUMPTION  - Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	VOLTAGE	5 V ± 10 %		
POWER CONSUMPTION  - Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption				
POWER CONSUMPTION  - Write: 270mA max Slumber: less than 100mA  FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption				
FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption				
FEATURE LIST  - In-House Designed Controller (HW/FW) - Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	POWER CONSUMPTION			
FEATURES & TOOLS  - In-House Designed Controller (HW/FW)  - Power Fail Data Safety  - Power Back-up Circuit  - Global static wear leveling  - SMART  - NCQ, TRIM  - AES 128/256bit encryption		- Slumber: less than 100mA		
FEATURES & TOOLS  - In-House Designed Controller (HW/FW)  - Power Fail Data Safety  - Power Back-up Circuit  - Global static wear leveling  - SMART  - NCQ, TRIM  - AES 128/256bit encryption				
- In-House Designed Controller (HW/FW)  - Power Fail Data Safety  - Power Back-up Circuit  - Global static wear leveling  - SMART  - NCQ, TRIM  - AES 128/256bit encryption				
- Power Fail Data Safety - Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption	FEATURE LIST			
- Power Back-up Circuit - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption				
FEATURES & TOOLS  - Global static wear leveling - SMART - NCQ, TRIM - AES 128/256bit encryption				
- SMART - NCQ, TRIM - AES 128/256bit encryption	FEATURES & TOOLS			
- NCQ, TRIM - AES 128/256bit encryption	- PEATONEO & TOOLS			
- AES 128/256bit encryption				
	PART NUMBER	SHE1BxxxxTXDxB00SSA0	SHE1BxxxxTxDxB00SSA0	



# **ПОСТАВКА** ЭЛЕКТРОННЫХ КОМПОНЕНТОВ

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001 Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

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Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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